

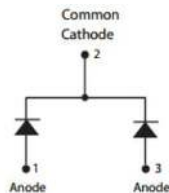
## MBR20200WT SCHOTTKY RECTIFIER



### Features

- 150 °C T<sub>J</sub> operation
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- This is a Pb – Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

### Circuit Diagram



### Applications

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection
- Center tap configuration

### Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V <sub>RRM</sub> V <sub>RWM</sub> V <sub>R</sub>	-	200	V
Average Rectified Forward Current	I <sub>F(AV)</sub>	50% duty cycle @T <sub>c</sub> =125°C, rectangular wave form	10(Per Leg) 20(Per Device)	A
Peak One Cycle Non-Repetitive Surge Current(Per Leg)	I <sub>FSM</sub>	8.3ms, Half Sine pulse	180	A

### Electrical Characteristics:

Characteristics	Symbol	Condition	Typ.	Max.	Units
Forward Voltage Drop (Per Leg)*	V <sub>F1</sub>	@ 10A, Pulse, T <sub>J</sub> = 25 °C	0.85	0.90	V
	V <sub>F2</sub>	@ 10A, Pulse, T <sub>J</sub> = 125 °C	0.75	0.80	V
Reverse Current (Per Leg)*	I <sub>R1</sub>	@V <sub>R</sub> = rated V <sub>R</sub> Pulse T <sub>J</sub> = 25 °C	0.001	1.0	mA
	I <sub>R2</sub>	@V <sub>R</sub> = rated V <sub>R</sub> , Pulse T <sub>J</sub> = 125 °C	0.1	50	mA
Junction Capacitance(Per Leg)	C <sub>T</sub>	@V <sub>R</sub> = 5V, T <sub>C</sub> = 25 °C f <sub>sig</sub> = 1MHz	110	500	pF
Voltage Rate of Change	dv/dt	-	-	10,000	V/μs

\* Pulse width < 300 μs, duty cycle < 2%

**Thermal-Mechanical Specifications:**

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	$T_J$	-	-55 to +150	$^{\circ}\text{C}$
Storage Temperature	$T_{\text{stg}}$	-	-55 to +150	$^{\circ}\text{C}$
Typical Thermal Resistance Case to heatsink	$R_{\theta\text{JCH}}$	DC operation	2	$^{\circ}\text{C}/\text{W}$
Approximate Weight	wt	-	6.28	g
Case Style	TO-247AD			

**Ratings and Characteristics Curves**

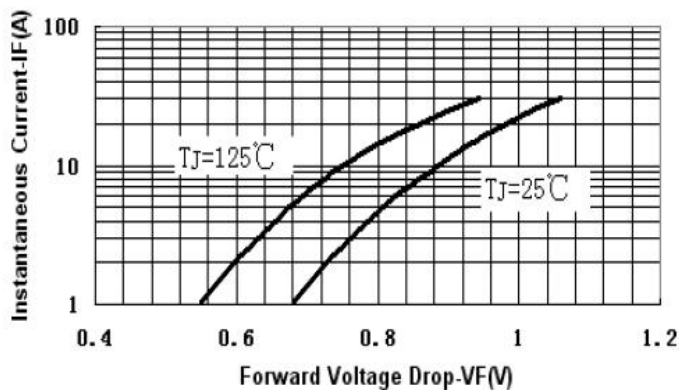


Fig.1-Typical Forward Voltage Drop Characteristics

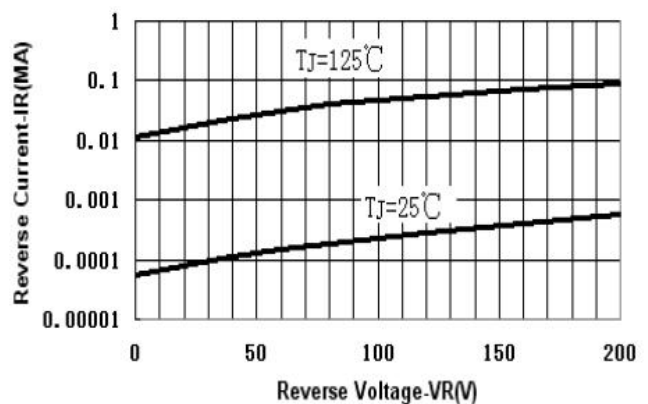


Fig.2-Typical Values Of Reverse Current Vs.Reverse Voltage

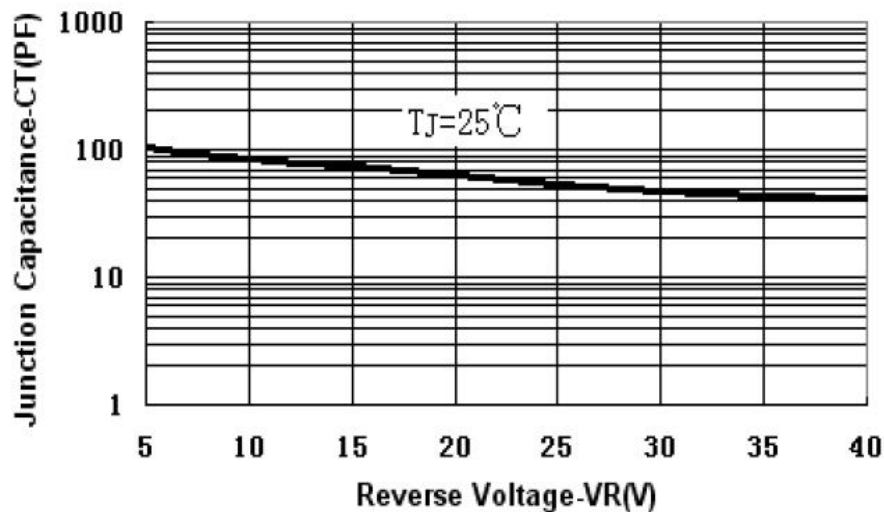
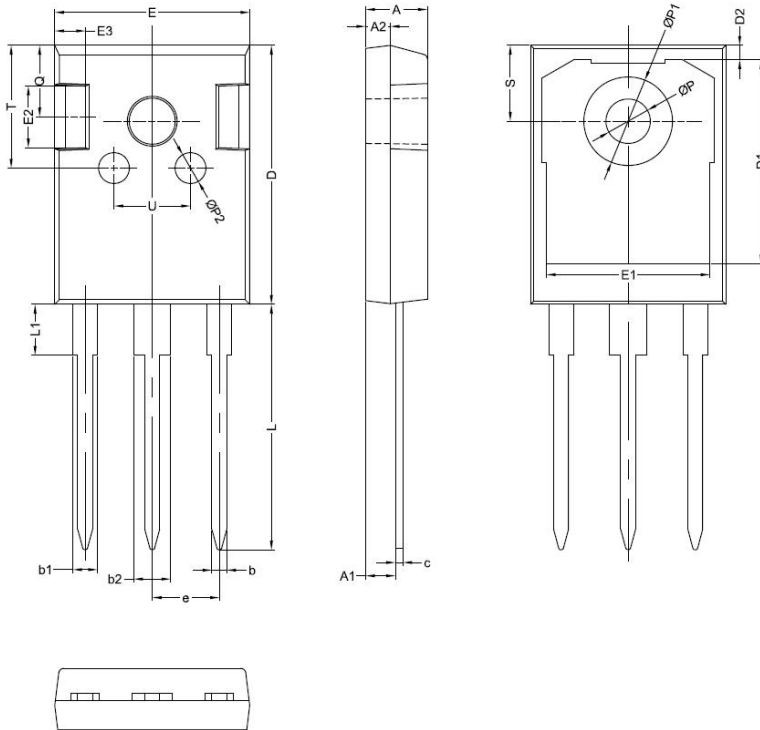


Fig.3-Typical Junction Capacitance Vs.Reverse Voltage

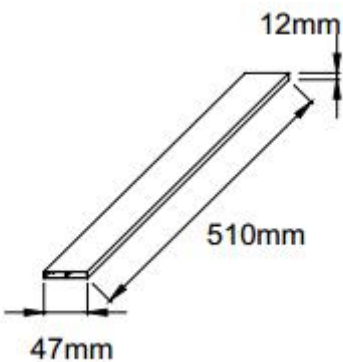
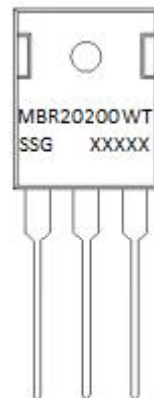
**Mechanical Dimensions TO-247AD**


SYMBOL	Millimeters		
	MIN.	TYP.	MAX.
A	4.80	5.00	5.20
A1	2.20	2.41	2.61
A2	1.90	2.00	2.10
b	1.10	1.20	1.40
b1	1.80	2.00	2.20
b2	2.80	3.00	3.20
c	0.50	0.60	0.75
D	20.30	21.00	21.20
D1		16.55	
D2		1.20	
E	15.45	15.80	16.00
E1		13.30	
E2		5.00	
E3		2.50	
e		5.44	
L	19.42	19.92	20.70
L1		4.13	
P	3.50	3.60	3.70
P1	7.1		7.40
P2		2.50	
Q		5.80	
S	6.05	6.15	6.25
T		10.00	
U		6.20	

**Ordering Information:**

Device	Package	Shipping
MBR20200WT	TO-247AD(Pb-Free)	25pcs / tube

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

**Tube Specification**

**Marking Diagram**


Where XXXXX is YYWWL

- MBR = Device Type
- 20 = Forward Current (20A)
- 200 = Reverse Voltage (200V)
- WT = Configuration
- SSG = SSG
- YY = Year
- WW = Week
- L = Lot Number

**Cautions:** Molding resin  
Epoxy resin UL:94V-0

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